

2N2906 2N2906A  
2N2907 2N2907A

**PNP SILICON TRANSISTOR**



**TO-18 CASE**



[www.centrasemi.com](http://www.centrasemi.com)

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR 2N2906, 2N2907 series types are silicon PNP epitaxial planar transistors designed for small signal, general purpose switching applications.

**MARKING: FULL PART NUMBER**

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

Collector-Base Voltage  
Collector-Emitter Voltage  
Emitter-Base Voltage  
Continuous Collector Current  
Power Dissipation  
Power Dissipation ( $T_C=25^\circ\text{C}$ )  
Operating and Storage Junction Temperature  
Thermal Resistance  
Thermal Resistance

SYMBOL	2N2906	2N2906A	UNITS
	2N2907	2N2907A	
$V_{CB0}$	60	60	V
$V_{CEO}$	40	60	V
$V_{EBO}$		5.0	V
$I_C$		600	mA
$P_D$		400	mW
$P_D$		1.8	W
$T_J, T_{stg}$		-65 to +200	$^\circ\text{C}$
$\theta_{JA}$		438	$^\circ\text{C/W}$
$\theta_{JC}$		97	$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	2N2906		2N2906A		UNITS
		2N2907		2N2907A		
		MIN	MAX	MIN	MAX	
$I_{CBO}$	$V_{CB}=50\text{V}$	-	20	-	10	nA
$I_{CBO}$	$V_{CB}=50\text{V}, T_A=150^\circ\text{C}$	-	20	-	10	$\mu\text{A}$
$I_{CEV}$	$V_{CE}=30\text{V}, V_{EB}=0.5\text{V}$	-	50	-	50	nA
$BV_{CBO}$	$I_C=10\mu\text{A}$	60	-	60	-	V
$BV_{CEO}$	$I_C=10\text{mA}$	40	-	60	-	V
$BV_{EBO}$	$I_E=10\mu\text{A}$	5.0	-	5.0	-	V
$V_{CE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$	-	0.4	-	0.4	V
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$	-	1.6	-	1.6	V
$V_{BE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$	-	1.3	-	1.3	V
$V_{BE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$	-	2.6	-	2.6	V
$f_T$	$V_{CE}=20\text{V}, I_C=50\text{mA}, f=100\text{MHz}$	200	-	200	-	MHz
$C_{ob}$	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$	-	8.0	-	8.0	pF
$C_{ib}$	$V_{EB}=2.0\text{V}, I_C=0, f=1.0\text{MHz}$	-	30	-	30	pF
$t_{on}$	$V_{CC}=30\text{V}, I_C=150\text{mA}, I_{B1}=15\text{mA}$	-	45	-	45	ns
$t_{off}$	$V_{CC}=6.0\text{V}, I_C=150\text{mA}, I_{B1}=I_{B2}=15\text{mA}$	-	100	-	100	ns

2N2906 2N2906A  
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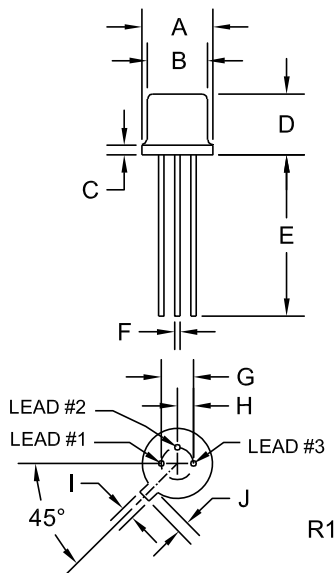
PNP SILICON TRANSISTOR



ELECTRICAL CHARACTERISTICS - Continued: ( $T_A=25^\circ\text{C}$ )

SYMBOL	TEST CONDITIONS	2N2906 2N2906A		2N2907 2N2907A	
		MIN	MAX	MIN	MAX
hFE	$V_{CE}=10\text{V}$ , $I_C=0.1\text{mA}$ (2N2906, 2N2907)	20	-	35	-
hFE	$V_{CE}=10\text{V}$ , $I_C=0.1\text{mA}$ (2N2906A, 2N2907A)	40	-	75	-
hFE	$V_{CE}=10\text{V}$ , $I_C=1.0\text{mA}$ (2N2906, 2N2907)	25	-	50	-
hFE	$V_{CE}=10\text{V}$ , $I_C=1.0\text{mA}$ (2N2906A, 2N2907A)	40	-	100	-
hFE	$V_{CE}=10\text{V}$ , $I_C=10\text{mA}$ (2N2906, 2N2907)	35	-	75	-
hFE	$V_{CE}=10\text{V}$ , $I_C=10\text{mA}$ (2N2906A, 2N2907A)	40	-	100	-
hFE	$V_{CE}=10\text{V}$ , $I_C=150\text{mA}$	40	120	100	300
hFE	$V_{CE}=10\text{V}$ , $I_C=500\text{mA}$ (2N2906, 2N2907)	20	-	30	-
hFE	$V_{CE}=10\text{V}$ , $I_C=500\text{mA}$ (2N2906A, 2N2907A)	40	-	50	-

TO-18 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.209	0.230	5.31	5.84
B (DIA)	0.178	0.195	4.52	4.95
C	-	0.030	-	0.76
D	0.170	0.210	4.32	5.33
E	0.500	-	12.70	-
F (DIA)	0.016	0.019	0.41	0.48
G (DIA)	0.100		2.54	
H	0.050		1.27	
I	0.036	0.046	0.91	1.17
J	0.028	0.048	0.71	1.22

TO-18 (REV: R1)

LEAD CODE:

- 1) Emitter
- 2) Base
- 3) Collector

MARKING: FULL PART NUMBER

R4 (30-January 2012)